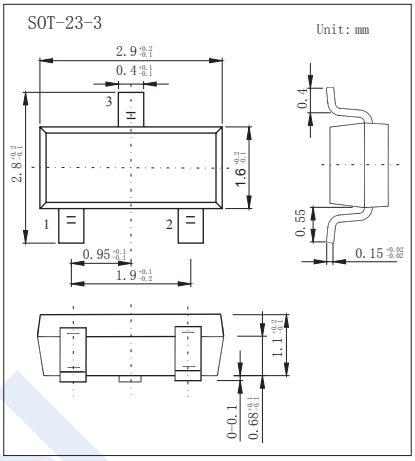
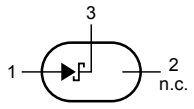
Schottky Diodes

BAS70/A/C/S (KAS70/A/C/S)

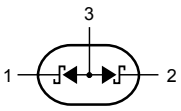


■ Features

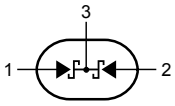
- Fast Switching Speed
- High breakdown voltage



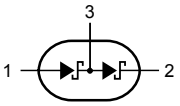
BAS70 single diode.



BAS70A



BAS70C



BAS70-S

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	70	V
Peak Reverse Voltage	V_{RRM}	70	
Average Rectified Current at Temp=25℃	I_{FAV}	200	mA
Non-Repetitive Peak Forward Surge Current t=1s	I_{FSM}	600	
Power Dissipation	P_d	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 10 uA	70			V
Forward voltage	V_{F1}	I_F= 1 mA			0.41	
	V_{F2}	I_F= 10 mA			0.75	
	V_{F3}	I_F= 15 mA			1	
Reverse voltage leakage current	I_{R1}	V_R= 70 V			1	uA
	I_{R2}	V_R= 50 V			0.1	
Junction capacitance	C_j	V_R= 0 V, f= 1 MHz			2	pF

■ Marking

NO.	BAS70	BAS70A	BAS70C	BAS70S
Marking	A70	A72	A73	A74

Schottky Diodes

BAS70/A/C/S (KAS70/A/C/S)

■ Typical Characterisitics

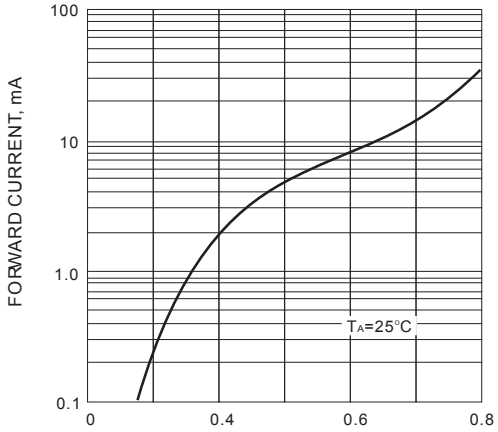


FIG. 1-TYPICAL FORWARD CHARACTERISTIC

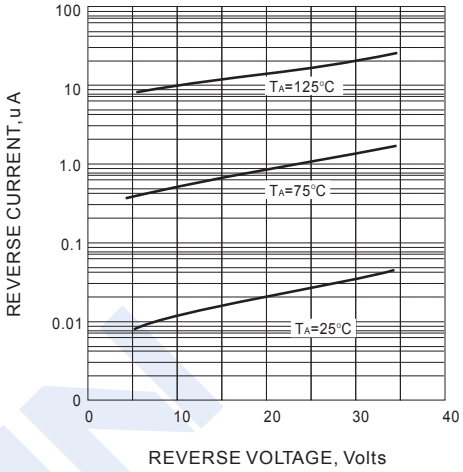


FIG. 2-TYPICAL REVERSE CHARACTERISTICS

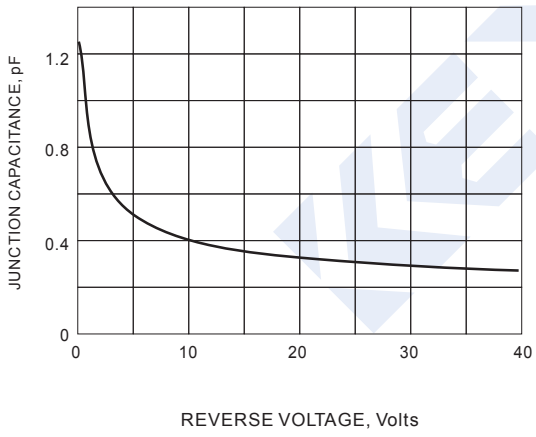


FIG. 3 TYPICAL JUNCTION CAPACITANCE

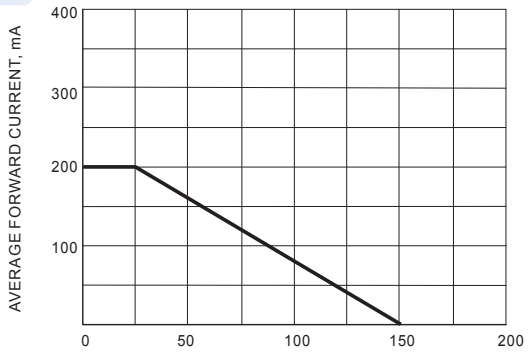


FIG. 4 FORWARD CURRENT DERATING